2829

PATENT
30205/37916

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Jae Hong Kim and Sang Ick Lee

Serial No.: 10/038,375

Filed: January 4, 2002

For: Chemical Mechanical Polishing Slurry and Process for Ruthenium Films

Group Art Unit: 2829

Examiner: Asok K. Sarkar

I hereby certify that this paper and the documents referred to as enclosed therewith are being deposited with the United States Postal Service as first class mail, postage prepaid, on **January 21, 2003**, in an envelope addressed to Commissioner for Patents, Washington, D.C. 20231.

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AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the office action mailed on October 22, 2002, please amend the above-identified patent application, as follows:

In the Specification:

Please replace the paragraph beginning on page 6, line 8, with the following rewritten paragraph:

--In more detail, the slurry containing about 2 wt% of HNO_3 and about 2 wt% of ceric ammonium nitrate has a polishing rate of about 600 Å/min under a polishing pressure of 1 psi; the slurry containing about 2 wt% of HNO_3 and about 6 wt% of ceric ammonium nitrate has a polishing rate of about 1200 Å/min under a polishing pressure of 1 psi; the slurry containing about 2 wt% of HNO_3 and about 10 wt% of ceric ammonium nitrate has a polishing rate of about 1400 Å/min under a polishing pressure of 1 psi; the slurry containing about 6 wt% of HNO_3 and about 2 wt% of ceric ammonium nitrate has a polishing rate of about 1050 Å/min under a polishing pressure of 1 psi; and the slurry containing about 10 wt% of HNO_3 and about 2 wt% of ceric ammonium nitrate has a polishing rate of about 1200 Å/min under a polishing pressure of 1 psi.--